



### 150-mW STEREO AUDIO POWER AMPLIFIER

#### **FEATURES**

- 150 mW Stereo Output
- **Differential Inputs**
- **PC Power Supply Compatible** 
  - Fully Specified for 3.3 V and 5 V Operation
  - Operation to 2.5 V
- **Pop Reduction Circuitry**
- **Internal Mid-Rail Generation**
- Thermal and Short-Circuit Protection
- **Surface-Mount Packaging** 
  - PowerPAD™ MSOP

#### $V_01$ $\coprod V_{\mathsf{DD}}$ IN1-2 9 $V_{0}$ 2 IN2-IN1+ 3 8 BYPASS [ TIN2+ GND **TSHUTDOWN** 勝 特 力 材 料 886-3-5753170 胜特力电子(上海) 86-21-34970699

胜特力电子(深圳) 86-755-83298787 Http://www.100y.com.tw

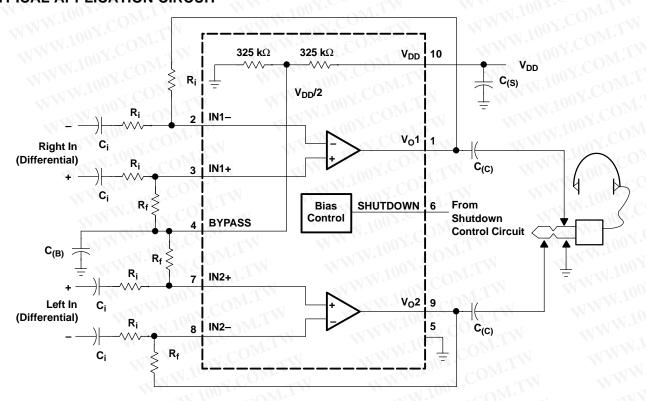
**DGQ PACKAGE** 

(TOP VIEW)

### DESCRIPTION

The TPA6112A2 is a stereo audio power amplifier with differential inputs packaged in a 10-pin PowerPAD MSOP package capable of delivering 150 mW of continuous RMS power per channel into 16-Ω loads. Amplifier gain is externally configured by means of two resistors per input channel and does not require external compensation for settings of 1 to 10.

### TYPICAL APPLICATION CIRCUIT



Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.

PowerPAD is a trademark of Texas Instruments.





These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

### **DESCRIPTION (CONTINUED)**

THD+N when driving an 16- $\Omega$  load from 5 V is 0.03% at 1 kHz, and less than 1% across the audio band of 20 Hz to 20 kHz. For 32- $\Omega$  loads, the THD+N is reduced to less than 0.02% at 1 kHz, and is less than 1% across the audio band of 20 Hz to 20 kHz. For 10-kΩ loads, the THD+N performance is 0.005% at 1 kHz, and less than 0.5% across the audio band of 20 Hz to 20 kHz.

### **AVAILABLE OPTIONS**

	T <sub>A</sub> 00	PACKAGED DEVICE  MSOP <sup>(1)</sup>	MSOP SYMBOLIZATION
-40°	C to 85°C	TPA6112A2DGQ	TI APD

(1) The DGQ package isavailable in left-ended tape and reel only (e.g., TPA6112A2DGQR).

### Terminal Functions

TERMINA NAME	AL NO	1/0	DESCRIPTION
BYPASS	4		Tap to voltage divider for internal mid-supply bias supply. Connect to a 0.1 $\mu$ F to 1 $\mu$ F low ESR capacitor for best performance.
GND	5	L	GND is the ground connection.
IN1-	2	$M_{I_{I}}$	IN1- is the negative input for channel 1.
IN1+	3		IN1+ is the positive input for channel 1.
IN2-	8 C	J'i	IN2- is the negative input for channel 2.
IN2+	7		IN2+ is the positive input for channel 2.
SHUTDOWN	6		Puts the device in a low quiescent current mode when held high.
$V_{DD}$	10		V <sub>DD</sub> is the supply voltage terminal.
V <sub>O</sub> 1	1	0	V <sub>O</sub> 1 is the audio output for channel 1.
V <sub>O</sub> 2	9	0	V <sub>O</sub> 2 is the audio output for channel 2.

#### ABSOLUTE MAXIMUM RATINGS

over operating free-air temperature (unless otherwise  $noted^{(1)}$ )

	WW. 100X. CALLEN WITH THE TOTAL ON THE	UNITS
$V_{DD}$	Supply voltage	6 V
V <sub>I</sub>	Input voltage	-0.3 V to V <sub>DD</sub> + 0.3 V
	Continuous total power dissipation	internally limited
TJ	Operating junction temperature range	-40°C to 150°C
T <sub>stg</sub>	Storage temperature range	-65°C to 150°C
	Lead temperature 1,6 mm (1/16 inch) from case for 10 seconds	260°C

(1) Stresses beyond thoselisted under absolute maximum ratings may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at theseor any other conditions beyond those indicated under recommended operating conditions is not implied. Exposure to absolute-maximum-rated conditions forextended periods may affect device reliability.



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### DISSIPATION RATING TABLE

PACKAGE	T <sub>A</sub> ≤ 25°C	DERATING FACTOR	T <sub>A</sub> = 70°C	T <sub>A</sub> = 85°C
	POWER RATING	ABOVE T <sub>A</sub> = 25°C	POWER RATING	POWER RATING
DGQ	2.14 W <sup>(1)</sup>	17.1 mW/°C	1.37 W	1.11 W

(1) Please see the Texas Instrumentsdocument, PowerPAD Thermally EnhancedPackage Application Report (literature number SLMA002), for moreinformation on the PowerPAD package. The thermal data was measured on a PCBlayout based on the information in the section entitled Texas Instruments Recommended Board for PowerPAD on page 200

### RECOMMENDED OPERATING CONDITIONS

5 V
5 °C
,
V
V <sub>DD</sub> V
(

DC ELECTRICAL CHARACTERISTICS  At T <sub>A</sub> = 25°C, V <sub>DD</sub> = 2.5 V (Unless Otherwise Noted)					
M.M.	PARAMETER	TEST CONDITIONS	MIN TYP	MAX	UNIT
Voo	Output offset voltage	A <sub>V</sub> = 2 V/V	100X.Co.	15	mV
PSRR	Power supply rejection ratio	V <sub>DD</sub> = 3.2 V to 3.4 V	83	Mrs	√ dB
I <sub>DD</sub>	Supply current	SHUTDOWN = 0 V	1.5	3	mA
I <sub>DD(SD)</sub>	Supply current in SHUTDOWN mode	SHUTDOWN = V <sub>DD</sub>	10	50	μA
Z <sub>i</sub>	Input impedance	· CO CO	>1		ΜΩ

### **AC OPERATING CHARACTERISTICS**

$V_{\rm DD} = 3.3$	$8 \text{ V}, \text{ T}_{\text{A}} = 25^{\circ}\text{C}, \text{ R}_{\text{L}} = 16 \Omega$	· CON	THE STATE OF THE S	V.C.	111-
	PARAMETER	TEST CONDITIONS	MIN TYP	MAX	UNIT
Po	Output power (each channel)	THD≤ 0.1%, f = 1 kHz	60	101.0	mW
THD+N	Total harmonic distortion + noise	P <sub>O</sub> = 40 mW, 20 - 20 kHz	0.4%	onY.	
B <sub>OM</sub>	Maximum output power BW	G = 10, THD < 5%	> 20	100	kHz
	Phase margin	Open loop	96°	700 .	- 001
	Supply ripple rejection ratio	f = 1 kHz	71	1100	dB
	Channel/channel output separation	f = 1 kHz	89	4	dB
SNR	Signal-to-noise ratio	$P_{O} = 50 \text{ mW}, A_{V} = 1$	100	M'In	dB
V <sub>n</sub>	Noise output voltage	A <sub>V</sub> = 1	11	-xxi 1	μV(rms

### DC ELECTRICAL CHARACTERISTICS

DC ELE	C ELECTRICAL CHARACTERISTICS						
At T <sub>A</sub> = 25°C, V <sub>DD</sub> = 5 .5 V (Unless otherwise noted)							
	PARAMETER	TEST CONDITIONS	MIN TYP	MAX	UNIT		
Voo	Output offset voltage	A <sub>V</sub> = 2 V/V	1100Y.C.M.TW	15	mV		
PSRR	Power supply rejection ratio	V <sub>DD</sub> = 4.9 V to 5.1 V	76	V	dB		
I <sub>DD</sub>	Supply current	SHUTDOWN = 0 V	1.5	3	mA		
I <sub>DD(SD)</sub>	Supply current in SHUTDOWN mode	SHUTDOWN = V <sub>DD</sub>	60	100	μA		
I <sub>IH</sub>	High-level input current (SHUTDOWN)	$V_{DD} = 5.5 \text{ V}, V_{I} = V_{DD}$	W. 100Y.	1	μA		
I <sub>IL</sub>	Low-level input current (SHUTDOWN)	$V_{DD} = 5.5 \text{ V}, V_{I} = 0 \text{ V}$	MM. OOX.CO	1	μΑ		
Z <sub>i</sub>	Input impedance	COM.	-XXV.100 - C(>1)1.		МΩ		



### **AC OPERATING CHARACTERISTICS**

$V_{DD} = 5 \ $	I, T <sub>A</sub> = 25°C, R <sub>L</sub> = 16 Ω			
MIT	PARAMETER	TEST CONDITIONS	MIN TYP MAX	UNIT
Po	Output power (each channel)	THD≤ 0.1%, f = 1 kHz	150	mW
THD+N	Total harmonic distortion + noise	P <sub>O</sub> = 100 mW, 20 - 20 kHz	0.6%	
B <sub>OM</sub>	Maximum output power BW	G = 10, THD < 5%	> 20	kHz
MOD	Phase margin	Open loop	96°	
	Supply ripple rejection ratio	f = 1 kHz	61	dB
V.COP	Channel/channel output separation	f = 1 kHz	90	dB
SNR	Signal-to-noise ratio	P <sub>O</sub> = 100 mW, A <sub>V</sub> = 1	100	dB
V <sub>n</sub>	Noise output voltage	A <sub>V</sub> = 1	11.7	μV(rms

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## AC OPERATING CHARACTERISTICS

1.100.	PARAMETER	TEST CONDITIONS	MIN TYP	MAX UN
Po (00	Output power (each channel)	THD≤ 0.1%, f = 1 kHz	40	mV
THD+N	Total harmonic distortion + noise	P <sub>O</sub> = 30 mW, 20 - 20 kHz	0.4%	NA .
B <sub>OM</sub>	Maximum output power BW	A <sub>V</sub> = 10, THD < 2%	> 20	kH
1.W.	Phase margin	Open loop	96°	TIN
41	Supply ripple rejection ratio	f = 1 kHz	71	dE
MA	Channel/channel output separation	f = 1 kHz	95	dE
SNR	Signal-to-noise ratio	P <sub>O</sub> = 40 mW, A <sub>V</sub> = 1	100	√ N dE
V <sub>n</sub>	Noise output voltage	A <sub>V</sub> = 1	110	μV(rr

# AC OPERATING CHARACTERISTICS V<sub>DD</sub> = 5 V. T. - 25°C D

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Po	Output power (each channel)	THD≤ 0.1%, f = 1 kHz	TINV	90	47 C.C	mW
THD+N	Total harmonic distortion + noise	P <sub>O</sub> = 60 mW, 20 - 20 kHz	M.	0.4%	Jr.	OM.T
B <sub>OM</sub>	Maximum output power BW	A <sub>V</sub> = 10, THD < 2%	MW	> 20	OYIC	kHz
	Phase margin	Open loop	WV	97°	oov.	COM
	Supply ripple rejection ratio	f = 1 kHz	1	61	100	dB
	Channel/channel output separation	f = 1 kHz		98	700,	dB
SNR	Signal-to-noise ratio	$P_{O} = 90 \text{ mW}, A_{V} = 1$		100	- 100	dB
V <sub>n</sub>	Noise output voltage	A <sub>V</sub> = 1		11.7	N. ro	μV(rms)

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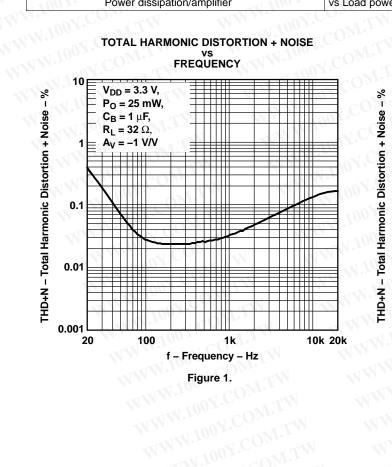
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### TYPICAL CHARACTERISTICS

WT	WWW.inov.Co.i.T	MM. 100xin	FIGURE
TUDIN	Total harmania distortion alva paisa	vs Frequency	1, 3, 5, 6, 7, 9, 11, 13
THD+N	Total harmonic distortion plus noise	vs Output power	2, 4, 8, 10, 12, 14
TIM	Supply ripple rejection ratio	vs Frequency	15, 16
$V_n$	Output noise voltage	vs Frequency	17, 18
COMP.	Crosstalk	vs Frequency	19 - 24
MOM.	Shutdown attenuation	vs Frequency	25, 26
OY.CO	Open-loop gain and phase margin	vs Frequency	27, 28
WY.COD	Output power	vs Load resistance	29, 30,
$I_{DD}$	Supply current	vs Supply voltage	.31
SNR	Signal-to-noise ratio	vs Voltage gain	32
1007.0	Power dissipation/amplifier	vs Load power	33, 34

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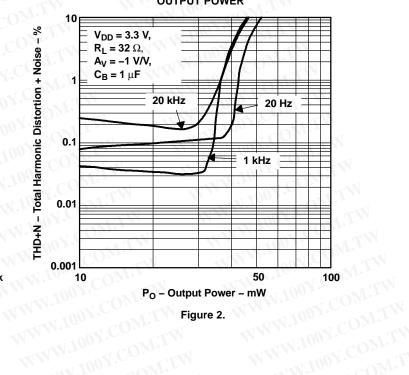


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### **TOTAL HARMONIC DISTORTION + NOISE** vs OUTPUT POWER

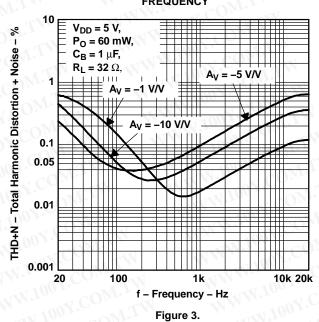


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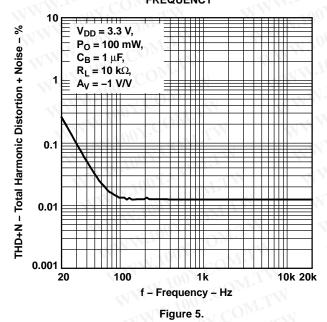
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### TOTAL HARMONIC DISTORTION + NOISE vs FREQUENCY

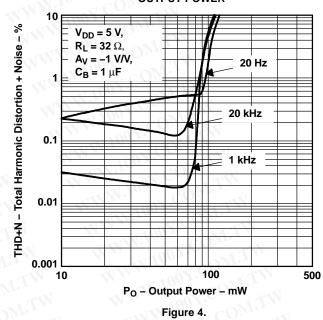


## TOTAL HARMONIC DISTORTION + NOISE vs FREQUENCY



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### TOTAL HARMONIC DISTORTION + NOISE vs OUTPUT POWER



## TOTAL HARMONIC DISTORTION + NOISE vs FREQUENCY

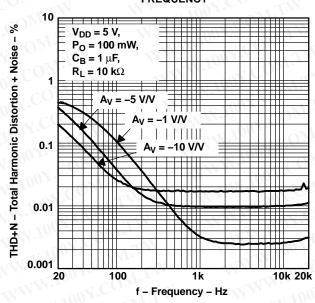
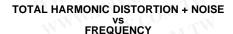
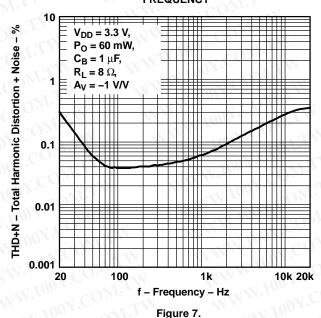


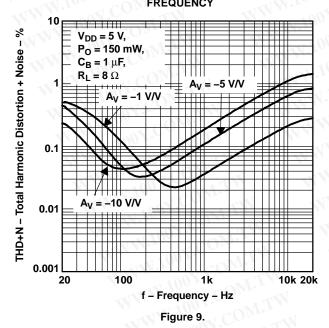
Figure 6.



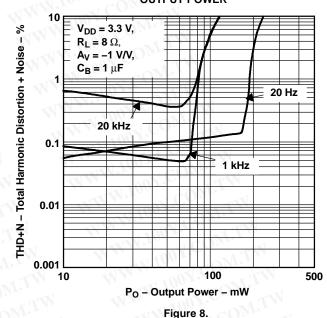




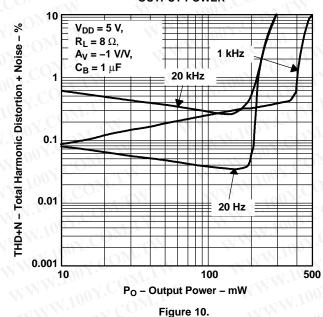
## TOTAL HARMONIC DISTORTION + NOISE vs FREQUENCY



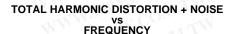
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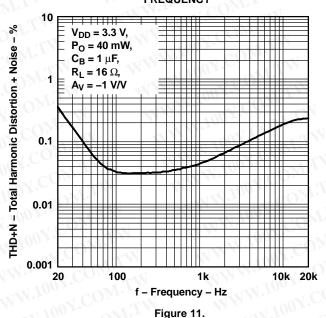


### TOTAL HARMONIC DISTORTION + NOISE vs OUTPUT POWER

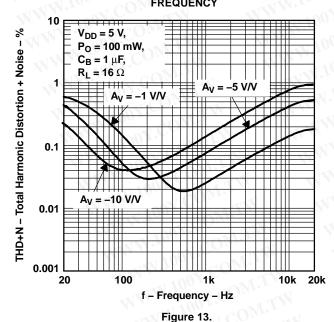




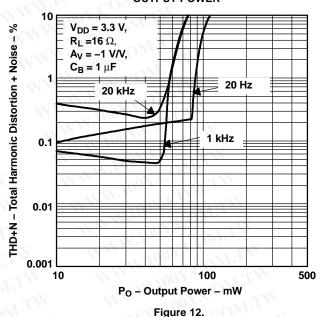




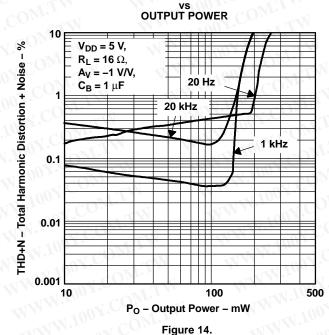
### TOTAL HARMONIC DISTORTION + NOISE vs FREQUENCY



### TOTAL HARMONIC DISTORTION + NOISE vs OUTPUT POWER



TOTAL HARMONIC DISTORTION + NOISE

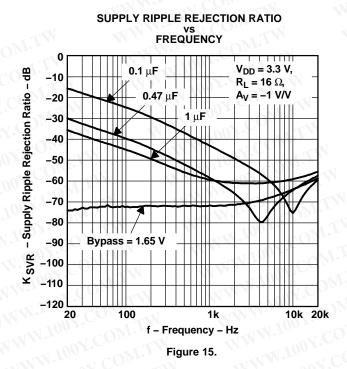


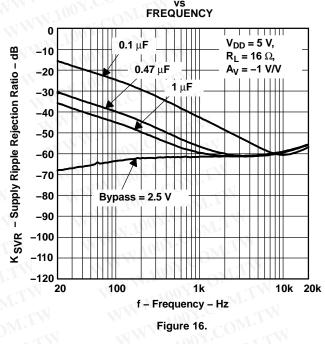
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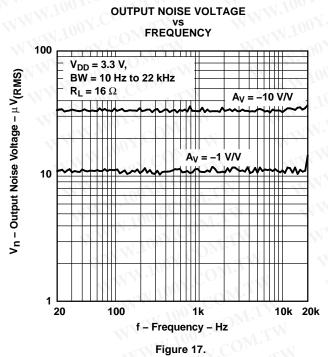
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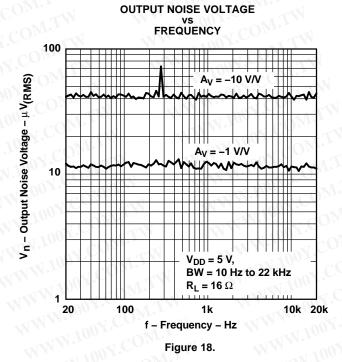
SUPPLY RIPPLE REJECTION RATIO





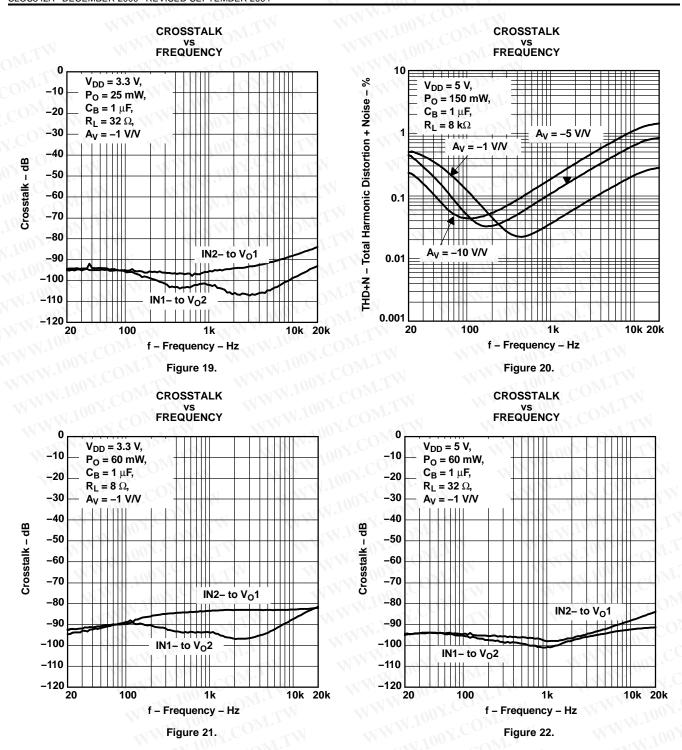






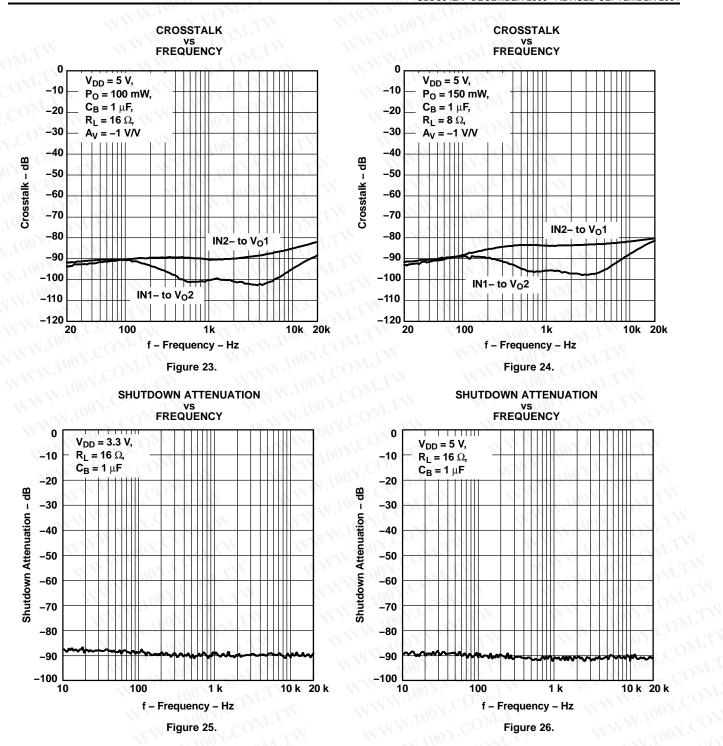
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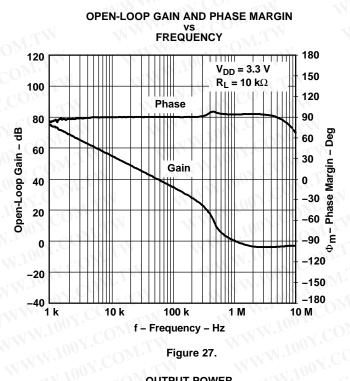


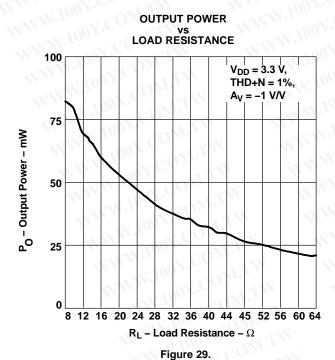


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**OPEN-LOOP GAIN AND PHASE MARGIN** vs FREQUENCY

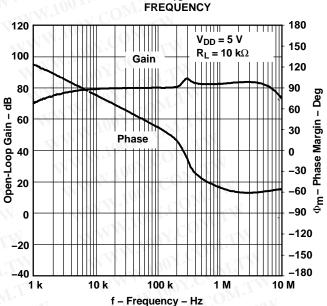
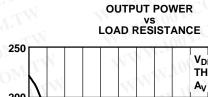


Figure 28.



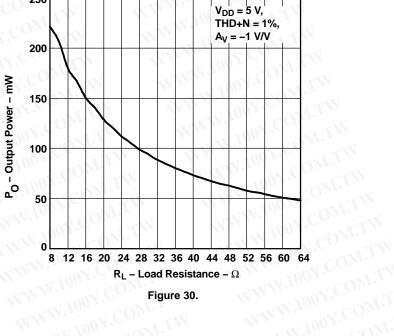


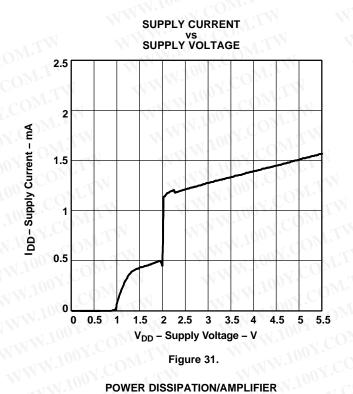
Figure 30.

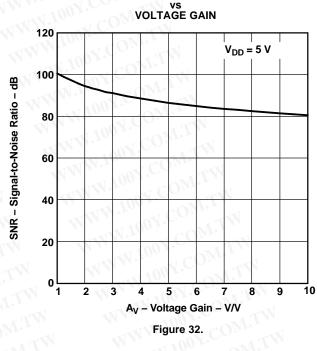
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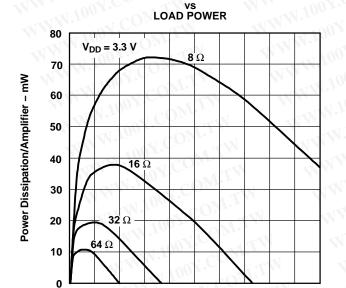
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**SIGNAL-TO-NOISE RATIO** 





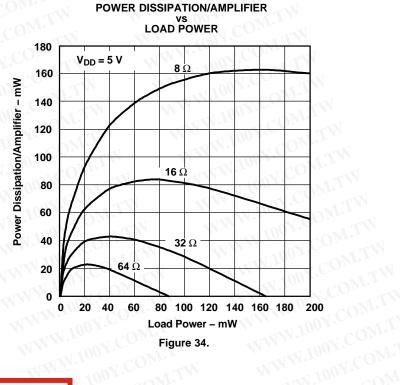




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80 100 120 140 160 180

Load Power - mW

Figure 33.



### **APPLICATION INFORMATION**

### GAIN SETTING RESISTORS, R, and Ri

The gain for the TPA6112A2 is set by resistors  $R_f$  and  $R_i$  according to Equation 1.

Gain 
$$\leq \times \stackrel{R_i}{R_i}$$
 (1)

Given that the TPA6112A2 is a MOS amplifier, the input impedance is very high. Consequently input leakage currents are not generally a concern. However, noise in the circuit increases as the value of  $R_{\rm f}$  increases. In addition, a certain range of  $R_{\rm f}$  values is required for proper start-up operation of the amplifier. Considering these factors, it is recommended that the effective impedance seen by the inverting node of the amplifier be set between 5 k $\Omega$  and 20 k $\Omega$ . The effective impedance is calculated using Equation 2.

Effective Impedance 
$$\leq \frac{R_f R_i}{R_f \times R_i}$$
 (2)

For example, if the input resistance is 20  $k\Omega$  and the feedback resistor is 20  $k\Omega,$  the gain of the amplifier is -1, and the effective impedance at the inverting terminal is 10  $k\Omega,$  a value within the recommended range.

For high performance applications, metal-film resistors are recommended because they tend to have lower noise levels than carbon resistors. For values of  $R_{\rm f}$  above 50  $k\Omega,$  the amplifier tends to become unstable due to a pole formed from  $R_{\rm f}$  and the inherent input capacitance of the MOS input structure. For this reason, a small compensation capacitor of approximately 5 pF should be placed in parallel with  $R_{\rm f}.$  This, in effect, creates a low-pass filter network with the cutoff frequency defined by Equation 3.

$$f_{c(lowpass)} \times \frac{1}{2\pi R_f C_F}$$
 (3)

For example, if  $R_{f}$  is 100  $k\Omega$  and  $C_{F}$  is 5 pF then  $f_{c(lowpass)}$  is 318 kHz, which is well outside the audio range.

### INPUT CAPACITOR, Ci

In the typical application, an input capacitor,  $C_i$ , is required to allow the amplifier to bias the input signal to the proper dc level for optimum operation. In this case,  $C_i$  and  $R_i$  form a high-pass filter with the corner frequency determined in Equation 4.

$$f_{c(highpass)} \times \frac{1}{2\pi R_i C_i}$$
 (4)

The value of  $C_i$  directly affects the bass (low frequency) performance of the circuit. Consider the example where  $R_i$  is 20 k $\Omega$  and the specification calls for a flat bass response down to 20 Hz. Equation 4 is reconfigured as Equation 5.

$$C_i \times \frac{1}{2\pi R_i f_{c(highpass)}}$$
 (5)

In this example,  $C_i$  is 0.40  $\mu F$ , so one would likely choose a value in the range of 0.47  $\mu F$  to 1  $\mu F$ . A further consideration for this capacitor is the leakage path from the input source through the input network formed by  $R_i$ ,  $C_i$ , and the feedback resistor ( $R_f$ ) to the load. This leakage current creates a dc offset voltage at the input to the amplifier that reduces useful headroom, especially in high-gain applications (gain >10). For this reason a low-leakage tantalum or ceramic capacitor is the best choice. When polarized capacitors are used, connect the positive side of the capacitor to the amplifier input in most applications. The dc level there is held at  $V_{DD}/2$ —likely higher than the source dc level. It is important to confirm the capacitor polarity in the application.

### POWER SUPPLY DECOUPLING, C(S)

The TPA6112A2 is a high-performance CMOS audio amplifier that requires adequate power-supply decoupling to minimize the output total harmonic distortion (THD). Power-supply decoupling also prevents oscillations when long lead lengths are used between the amplifier and the speaker. The optimum decoupling is achieved by using two capacitors of different types that target different types of noise on the power supply leads. For higher frequency transients, spikes, or digital hash on the line, a good low equivalent-series-resistance (ESR) ceramic capacitor, typically 0.1 µF, placed as close as possible to the device V<sub>DD</sub> lead, works best. For filtering lower-frequency noise signals, a larger aluminum electrolytic capacitor of 10 µF or greater placed near the power amplifier is recommended.



### MIDRAIL BYPASS CAPACITOR, C(B)

The midrail bypass capacitor,  $C_{(B)}$ , serves several important functions. During start up,  $C_{(B)}$  determines the rate at which the amplifier starts up. This helps to push the start-up pop noise into the subaudible range (so low it can not be heard). The second function is to reduce noise produced by the power supply caused by coupling into the output drive signal. This noise is from the midrail generation circuit internal to the amplifier. The capacitor is fed from a 230-k $\Omega$  source inside the amplifier. To keep the start-up pop as low as possible, maintain the relationship shown in Equation 6.

$$\frac{1}{\cancel{\$}_{(B)} \times 230 \text{ k}\Omega} \le \frac{1}{\cancel{\$}_{i}R_{i}}$$
(6)

Consider an example circuit where  $C_{(B)}$  is 1  $\mu F$ ,  $C_i$  is 1  $\mu F$ , and  $R_i$  is 20  $k\Omega$ . Substituting these values into the equation 9 results in:  $6.25 \le 50$  which satisfies the rule. Bypass capacitor,  $C_{(B)}$ , values of 0.1  $\mu F$  to 1  $\mu F$  ceramic or tantalum low-ESR capacitors are recommended for the best THD and noise performance.

### OUTPUT COUPLING CAPACITOR, C(C)

In a typical single-supply, single-ended (SE) configuration, an output coupling capacitor ( $C_{(C)}$ ) is required to block the dc bias at the output of the amplifier, thus preventing dc currents in the load. As with the input coupling capacitor, the output coupling capacitor and impedance of the load form a high-pass filter governed by Equation 7.

$$f_{C} \times \frac{1}{2\pi R_{L} C_{(C)}} \tag{7}$$

The main disadvantage, from a performance standpoint, is that the typically-small load impedance drives the low-frequency corner higher. Large values of  $C_{(C)}$  are required to pass low frequencies into the load. Consider the example where a  $C_{(C)}$  of 68  $\mu F$  is chosen and loads vary from 32  $\Omega$  to 47  $k\Omega.$  Table 1 summarizes the frequency response characteristics of each configuration.

Table 1. Common Load Impedances vs Low-Frequency Output Characteristics in SE Mode

$R_{L}$	C <sub>(C)</sub>	LOWEST FREQUENCY
32 Ω	68 µF	73 Hz
10,000 Ω	68 µF	0.23 Hz
47,000 Ω	68 µF	0.05 Hz

As Table 1 indicates, headphone response is adequate, and drive into line level inputs (a home stereo for example) is very good.

The output coupling capacitor required in single-supply SE mode also places additional constraints on the selection of other components in the amplifier circuit. With the rules described earlier still valid, add the following relationship:

$$\frac{1}{\left|C_{(B)} \times 230 \text{ k}\Omega\right|} \le \frac{1}{\left|C_{i}R_{i}\right|} \le \frac{1}{R_{L}C_{(C)}}$$
(8)

#### **USING LOW-ESR CAPACITORS**

Low-ESR capacitors are recommended throughout this application. A real capacitor can be modeled simply as a resistor in series with an ideal capacitor. The voltage drop across this resistor minimizes the beneficial effects of the capacitor in the circuit. The lower the equivalent value of this resistance, the more the real capacitor behaves like an ideal capacitor.

### **5-V VERSUS 3.3-V OPERATION**

The TPA6112A2 was designed for operation over a supply range of 2.5 V to 5.5 V. This data sheet provides full specifications for 5-V and 3.3-V operation, since these are considered to be the two most common supply voltages. There are no special considerations for 3.3-V versus 5-V operation as far as supply bypassing, gain setting, or stability. The most important consideration is that of output power. Each amplifier in theTPA6112A2 can produce a maximum voltage swing of  $V_{\rm DD}-1$  V. This means, for 3.3-V operation, clipping starts to occur when  $V_{\rm O(PP)}=2.3$  V as opposed when  $V_{\rm O(PP)}=4$  V while operating at 5 V. The reduced voltage swing subsequently reduces maximum output power into the load before distortion becomes significant.





4-Feb-2005

#### PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins F	Package Qty	Eco Plan <sup>(2)</sup>	Lead/Ball Finish	MSL Peak Temp <sup>(3)</sup>
TPA6112A2DGQ	ACTIVE	MSOP- Power PAD	DGQ	10	80	None	CU SNPB	Level-1-220C-UNLIM
TPA6112A2DGQR	ACTIVE	MSOP- Power PAD	DGQ	10	2500	None	CU SNPB	Level-1-220C-UNLIM
TPA6112A2DGQRG4	ACTIVE	MSOP- Power PAD	DGQ	10	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM

<sup>(1)</sup> The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) Eco Plan - May not be currently available - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.

None: Not yet available Lead (Pb-Free).

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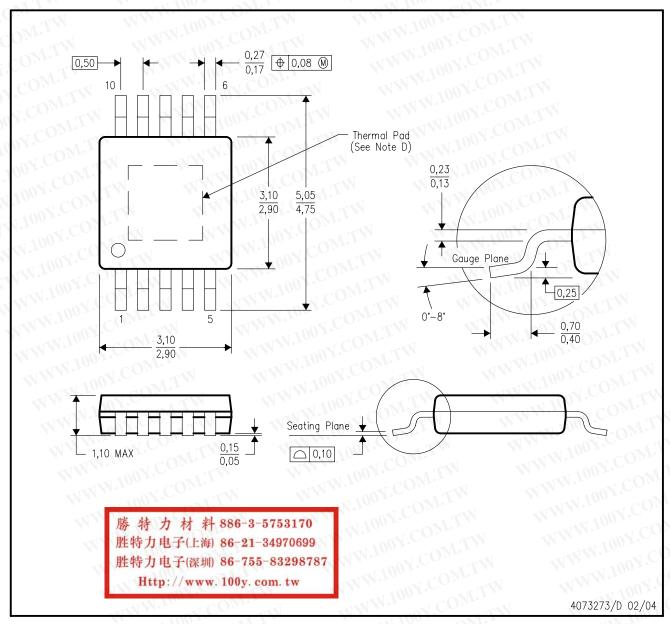
(3) MSL, Peak Temp. -- The Moisture Sensitivity Level rating according to the JEDECindustry standard classifications, and peak solder temperature.

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### DGQ (S-PDSO-G10) PowerPAD™ PLASTIC SMALL-OUTLINE PACKAGE



NOTES:

- A. All linear dimensions are in millimeters.
- B. This drawing is subject to change without notice.
- C. Body dimensions do not include mold flash or protrusion.
- D. This package is designed to be soldered to a thermal pad on the board. Refer to Technical Brief, PowerPad Thermally Enhanced Package, Texas Instruments Literature No. SLMA002 for information regarding recommended board layout. This document is available at www.ti.com <a href="https://www.ti.com">www.ti.com</a>.
- E. Falls within JEDEC MO-187 variation BA-T.

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Mailing Address: Texas Instruments

Post Office Box 655303 Dallas, Texas 75265

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